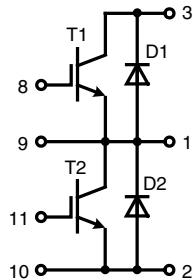


IGBT Module phaseleg

I_{C25} = 280 A
V_{CES} = 1200 V
V_{CE(sat)} typ. = 2.2 V

Preliminary data



IGBTs T1 - T2

Symbol	Conditions	Maximum Ratings		
V _{CES}	T _{VJ} = 25°C to 125°C	1200	V	
V _{GES}		± 20	V	
I _{C25}	T _C = 25°C	280	A	
I _{C80}	T _C = 80°C	200	A	
I _{CM}	V _{GE} = ±15 V; R _G = 7.5 Ω; T _{VJ} = 125°C	300	A	
V _{CEK}	RBSOA Clamped inductive load; L = 100 μH	V _{CES}		
t _{sc} (SCSOA)	V _{CE} = 900 V; V _{GE} = ±15 V; R _G = 7.5 Ω T _{VJ} = 125°C; non-repetitive	10	μs	
P _{tot}	T _C = 25°C	1100	W	

Symbol Conditions

Symbol	Conditions	Characteristic Values				
		(T _{VJ} = 25°C, unless otherwise specified)	min.	typ.	max.	
V _{CE(sat)}	I _C = 200 A; V _{GE} = 15 V;	T _{VJ} = 25°C T _{VJ} = 125°C		2.2 2.6	2.8	V
V _{GE(th)}	I _C = 6 mA; V _{GE} = V _{CE}		4.5	5.5	6.5	V
I _{CES}	V _{CE} = V _{CES} ; V _{GE} = 0 V;	T _{VJ} = 25°C T _{VJ} = 125°C		0.8 3.5	3.3	mA
I _{GES}	V _{CE} = 0 V; V _{GE} = ± 20 V			400	nA	
t _{d(on)} t _r t _{d(off)} t _f E _{on} E _{off}	Inductive load, T _{VJ} = 125°C V _{CE} = 600 V; I _C = 200 A V _{GE} = ±15 V; R _G = 7.5 Ω		170		ns	
			60		ns	
			680		ns	
			50		ns	
			29		mJ	
			20		mJ	
C _{ies}	V _{CE} = 25 V; V _{GE} = 0 V; f = 1 MHz		11		nF	
Q _{Gon}	V _{CE} = 600 V; V _{GE} = 15 V; I _C = 200 A		1.16		μC	
R _{thJC}	(per IGBT) with heatsink compound			0.11	K/W	
R _{thJH}			0.22		K/W	

Features

- NPT³ IGBT
 - low saturation voltage
 - positive temperature coefficient
 - fast switching
 - short tail current for optimized performance in resonant circuits
- HiPerFRED™ diodes
 - fast and soft reverse recovery
 - low operating forward voltage
 - low leakage current
- Package
 - low inductive current path
 - screw connection to high current main terminals
 - use of non interchangeable connectors for auxiliary terminals possible
 - kelvin emitter terminal for easy drive
 - isolated ceramic base plate

Applications

- drives
 - AC
 - DC
- power supplies
 - rectifiers with power factor correction and recuperation capability
 - UPS

Free wheeling diodes D1 - D2

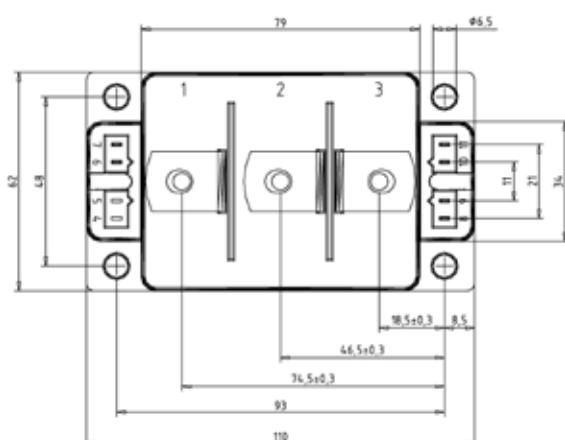
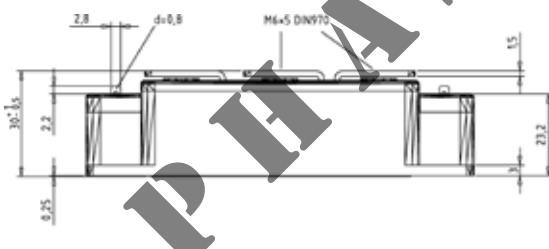
Symbol	Conditions	Maximum Ratings		
I _{F25}	T _C = 25°C	300	A	
I _{F80}	T _C = 80°C	190	A	

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
V _F	I _F = 200 A; V _{GE} = 0 V; T _{VJ} = 25°C T _{VJ} = 125°C		2.3 1.7	2.7 V V
I _{RM} t _{rr}	I _F = 150 A; dI _F /dt = 1500 A/μs; V _R = 600 V; V _{GE} = 0 V; T _{VJ} = 125°C		160 220	A ns
R _{thJC} R _{thJH}	(per IGBT) with heatsink compound		0.23 0.45	K/W K/W

Module

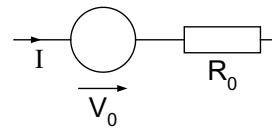
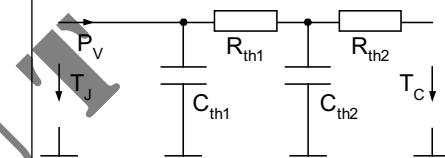
Symbol	Conditions	Maximum Ratings		
T _{VJ}	operating	-40...+150	°C	
T _{stg}		-40...+125	°C	
V _{ISO}	I _{ISOL} ≤ 1 mA; 50/60 Hz	4000	V~	
M _d	Mounting torque (module, M6) (terminal, M6)	2.25 - 2.75 4.5 - 5.5	Nm Nm	
Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
d _s d _A	Creepage distance on surface Strike distance in air	2 2		mm mm
Weight		250		g

Dimensions in mm (1 mm = 0.0394")



IXYS reserves the right to change limits, test conditions and dimensions.

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Equivalent Circuits for Simulation**Conduction**IGBT (typ. at V_{GE} = 15 V; T_J = 125°C)
V₀ = 1.0 V; R₀ = 8 mΩFree Wheeling Diode D1-D2 (typ. at T_J = 125°C)
V₀ = 1.3 V; R₀ = 2 mΩ**Thermal Response**

IGBT (typ.)

$$C_{th1} = tbd \text{ J/K}; R_{th1} = tbd \text{ K/W}$$

$$C_{th2} = tbd \text{ J/K}; R_{th2} = tbd \text{ K/W}$$

Free Wheeling Diode D1-D2 (typ.)

$$C_{th1} = tbd \text{ J/K}; R_{th1} = tbd \text{ K/W}$$

$$C_{th2} = tbd \text{ J/K}; R_{th2} = tbd \text{ K/W}$$

Optional accessories for moduleskeyed twin plugs
(UL758, style 1385, CSA class 5851,
guide 460-1-1)

- Type ZY180L with wire length 350mm
 - for pins 4 (yellow wire) and 5 (red wire)
 - for pins 11 (yellow wire) and 10 (red wire)
- Type ZY180R with wire length 350mm
 - for pins 7 (yellow wire) and 6 (red wire)
 - for pins 8 (yellow wire) and 9 (red wire)